- 1 1. A method comprising:
- aging a silica slurry for at least fifty days
- 3 from its manufacture date; and
- 4 using the aged slurry to chemical mechanical
- 5 polish a tantalum containing layer.
- 1 2. The method of claim 1 including using chemical
- 2 mechanical polishing with an aged slurry to form copper
- 3 metal lines.
- 1 3. The method of claim 1 including polishing through
- 2 a copper layer and a copper seed layer down to a tantalum
- 3 containing layer.
- 1 4. The method of claim 3 including polishing through
- 2 the tantalum containing layer down to a dielectric.
- 1 5. The method of claim 1 including using aged silica
- 2 slurries to reduce defects when polishing a tantalum
- 3 containing layer.
- 1 6. A method comprising:
- 2 receiving a silica slurry;
- determining its age from its date of manufacture;
- 4 and

- 5 when its age is greater than fifty days, using
- 6 the slurry to chemical mechanical polish a tantalum
- 7 containing layer.
- 7. The method of claim 6 including using chemical
- 2 mechanical polishing with an aged slurry to form copper
- 3 metal lines.
- 1 8. The method of claim 6 including polishing through
- 2 a copper layer and a copper seed layer down to a tantalum
- 3 containing layer.
- 1 9. The method of claim 8 including polishing through
- 2 the tantalum containing layer down to a dielectric.
- 1 10. The method of claim 6 including using an aged
- 2 silica slurry to reduce defects when polishing tantalum
- 3 containing layers.
- 1 11. A method comprising:
- aging a silica slurry for at least fifty days
- 3 from its data of manufacture; and
- 4 using the aged slurry to chemical mechanical
- 5 polish a metal layer.

- 1 12. The method of claim 11 including using the slurry
- 2 to polish a barrier layer.
- 1 13. The method of claim 12 including using the slurry
- 2 to polish a tantalum containing layer.
- 1 14. The method of claim 11 including using chemical
- 2 mechanical polishing with an aged slurry to form copper
- 3 metal lines.
- 1 15. The method of claim 11 including polishing
- 2 through a copper layer and a copper seed layer down to a
- 3 tantalum containing layer.
- 1 16. A method comprising:
- aging a slurry for at least fifty days from its
- 3 date of manufacture; and
- 4 using the aged slurry to chemical mechanical
- 5 polish a layer.
- 1 17. The method of claim 16 including aging a silica
- 2 slurry.
- 1 18. The method of claim 16 including using the aged
- 2 slurry to chemical mechanical polish a metal layer.

- 1 19. The method of claim 16 including using the aged
- 2 slurry to chemical mechanical polish a non-metal layer.
- 1 20. The method of claim 16 including aging a slurry
- 2 selected from the group including silica, alumina, and
- 3 ceria.